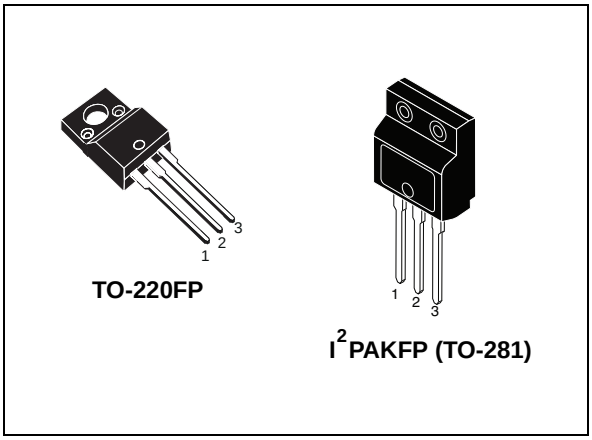
STF28N60M2, STFI28N60M2

N-channel 600 V, 0.135 Ω typ., 22 A MDmesh™ M2 Power MOSFETs in TO-220FP and I^2PAKFP packages

Datasheet - production data



TO-220FP

I^2PAKFP (TO-281)

Features

Order code	V_{DS} @ T_{Jmax}	$R_{DS(on)}$ max	I_D
STF28N60M2	650 V	0.150 Ω	22 A
STFI28N60M2			

- Extremely low gate charge
- Excellent output capacitance (C_{OSS}) profile
- 100% avalanche tested
- Zener-protected

Applications

- Switching applications
- LCC converters, resonant converters

Description

These devices are N-channel Power MOSFETs developed using MDmesh™ M2 technology. Thanks to their strip layout and improved vertical structure, the devices exhibit low on-resistance and optimized switching characteristics, rendering them suitable for the most demanding high efficiency converters.

Figure 1. Internal schematic diagram

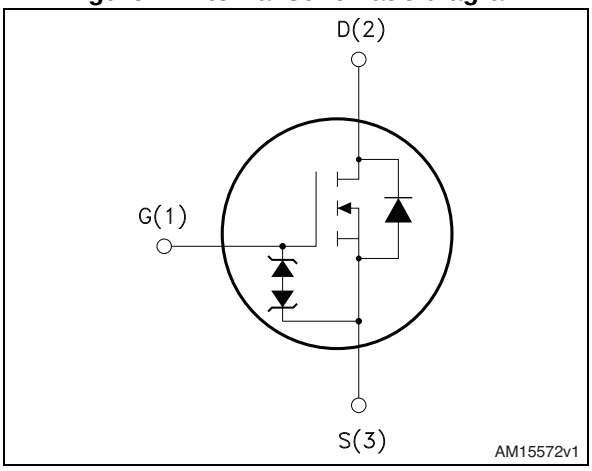


Table 1. Device summary

Order code	Marking	Package	Packaging
STF28N60M2	28N60M2	TO-220FP	Tube
STFI28N60M2		I^2PAKFP (TO-281)	

1 Electrical ratings

Table 2. Absolute maximum ratings

Symbol	Parameter	Value	Unit
V_{GS}	Gate-source voltage	± 25	V
I_D	Drain current (continuous) at T_C = 25 °C	22(1)	A
I_D	Drain current (continuous) at T_C = 100 °C	14(1)	A
I_{DM} (2)	Drain current (pulsed)	88(1)	A
P_{TOT}	Total dissipation at T_C = 25 °C	30	W
dv/dt (3)	Peak diode recovery voltage slope	15	V/ns
dv/dt(4)	MOSFET dv/dt ruggedness	50	V/ns
V_{ISO}	Insulation withstand voltage (RMS) from all three leads to external heat sink (t = 1 s; T_C = 25 °C)	2500	V
T_{stg}	Storage temperature	- 55 to 150	°C
T_j	Operating junction temperature		

1. Limited by maximum junction temperature.
2. Pulse width limited by safe operating area.
3. $I_{SD} \leq 22$ A, di/dt ≤ 400 A/µs; $V_{DS\ peak} < V_{(BR)DSS}$, V_{DD}= 400 V.
4. $V_{DS} \leq 480$ V

Table 3. Thermal data

Symbol	Parameter	Value	Unit
$R_{thj\text{-}case}$	Thermal resistance junction-case max	4.17	°C/W
$R_{thj\text{-}amb}$	Thermal resistance junction-ambient max	62.5	°C/W

Table 4. Avalanche characteristics

Symbol	Parameter	Value	Unit
I_{AR}	Avalanche current, repetitive or not repetitive (pulse width limited by T_{jmax})	3.6	A
E_{AS}	Single pulse avalanche energy (starting T_j=25°C, I_D= I_{AR}; V_{DD}=50V)	350	mJ

2 Electrical characteristics

(T_C = 25 °C unless otherwise specified)

Table 5. On /off states

Symbol	Parameter	Test conditions	Min.	Typ.	Max.	Unit
$V_{(BR)DSS}$	Drain-source breakdown voltage	I_D = 1 mA, V_{GS} = 0	600			V
I_{DSS}	Zero gate voltage drain current (V_{GS} = 0)	V_{DS} = 600 V			1	µA
		V_{DS} = 600 V, T_C=125 °C			100	µA
I_{GSS}	Gate-body leakage current (V_{DS} = 0)	V_{GS} = ± 25 V			±10	µA
$V_{GS(th)}$	Gate threshold voltage	V_{DS} = V_{GS}, I_D = 250 µA	2	3	4	V
$R_{DS(on)}$	Static drain-source on-resistance	V_{GS} = 10 V, I_D = 11 A		0.135	0.150	Ω

Table 6. Dynamic

Symbol	Parameter	Test conditions	Min.	Typ.	Max.	Unit
C_{iss}	Input capacitance	V_{DS} = 100 V, f = 1 MHz, V_{GS} = 0	-	1440	-	pF
C_{oss}	Output capacitance		-	70	-	pF
C_{rss}	Reverse transfer capacitance		-	2	-	pF
$C_{oss\ eq.}$ (1)	Equivalent output capacitance	V_{DS} = 0 to 480 V, V_{GS} = 0	-	104	-	pF
R_G	Intrinsic gate resistance	f = 1 MHz open drain	-	5.5	-	Ω
Q_g	Total gate charge	V_{DD} = 480 V, I_D = 22 A, V_{GS} = 10 V (see *Figure 15*)	-	36	-	nC
Q_{gs}	Gate-source charge		-	7.2	-	nC
Q_{gd}	Gate-drain charge		-	16	-	nC

1. $C_{oss\ eq.}$ is defined as a constant equivalent capacitance giving the same charging time as C_{oss} when V_{DS} increases from 0 to 80% V_{DSS}

Table 7. Switching times

Symbol	Parameter	Test conditions	Min.	Typ.	Max.	Unit
$t_{d(on)}$	Turn-on delay time	V_{DD} = 300 V, I_D = 11 A, R_G = 4.7 Ω, V_{GS} = 10 V (see *Figure 14* and *Figure 19*)	-	14.5	-	ns
t_r	Rise time		-	7.2	-	ns
$t_{d(off)}$	Turn-off delay time		-	100	-	ns
t_f	Fall time		-	8	-	ns

Table 8. Source drain diode

Symbol	Parameter	Test conditions	Min.	Typ.	Max.	Unit
I_{SD}	Source-drain current		-		22	A
I_{SDM} (1)	Source-drain current (pulsed)		-		88	A
V_{SD} (2)	Forward on voltage	I_{SD} = 22 A, V_{GS} = 0	-		1.6	V
t_{rr}	Reverse recovery time	I_{SD} = 22 A, di/dt = 100 A/µs V_{DD} = 60 V (see *Figure 19*)	-	350		ns
Q_{rr}	Reverse recovery charge		-	4.7		µC
I_{RRM}	Reverse recovery current		-	27		A
t_{rr}	Reverse recovery time	I_{SD} = 22 A, di/dt = 100 A/µs V_{DD} = 60 V, T_j = 150 °C (see *Figure 19*)	-	451		ns
Q_{rr}	Reverse recovery charge		-	6.5		µC
I_{RRM}	Reverse recovery current		-	29		A

1. Pulse width limited by safe operating area.
2. Pulsed: pulse duration = 300 µs, duty cycle 1.5%